

The role of phase separation in dynamics of charge system of half-doped manganites

V. Chabanenko¹, S. Vasiliev¹, A. Nabiałek², T. Tsvetkov¹, S. Dunaevsky³, R. Minikaev²,
S. Piechota², H. Szymczak², Z. Kravchenko¹

¹*Institute for Physics and Engineering, NASU, 72 Ul. R. Luxemburg, 83114, Donetsk, Ukraine.*

²*Institute of Physics, PAS, al. Lotników 32/46, O2-668 Warsaw, Poland*

³*Petersburg Nuclear Physics Institute, 188300, Gatchina, Russia*

Doped manganites are characterized by a strong interaction of the electron, lattice, and spin subsystems, resulting in diversified phase transitions and various types of ordering. Metal-insulator and structural transitions are observed as well as various types of magnetic, orbital, and charge orderings [1-3]. The interest in such materials has risen due to the dependence of the dielectric permittivity on the magnetic field [4]. The variation is maximal at around 270 K, little above the Curie temperature, T_C , and it reaches a value of 35% in $H = 0.5$ T. According to author's assumption, this phenomenon is due to the space-charge or interfacial polarization produced between the insulator and the metallic regions segregated intrinsically in the material above T_C .

In our experiments a sample of half-doped manganite $\text{La}_{0.5}\text{Ca}_{0.5}\text{Mn}_{0.94}\text{Fe}_{0.06}\text{O}_3$ was put into a capacitor and a complex admittance, $Y=G+iB$ (G - conductance, B - susceptance), of such system was studied in a wide range of temperatures (2 – 400 K) and magnetic fields (0 - 12 Tesla). The admittance was measured in a wide range of frequencies (20 – $2 \cdot 10^7$ Hz) using precision LCR meters. The magnetic field dependence of the conductance, $G(H)$, reveal pronounced peaks with the maxima corresponding to the beginning of the ferromagnetic transition. Two maxima are observed in the temperature dependence of the conductance $G(T)$.

These and other results are interpreted within a framework of a kinetic model taking into account the coexistence of ferromagnetic metal and antiferromagnetic dielectric domains as well as thermally activated transitions between these states.

[1] B. Raveau et al., J. Solid State Chem. 130 (1997) 162.

[2] F. Damay et al., Appl. Phys. Lett. 73 (1998) 3772.

[3] J.C. Loudon et al., Nature 420 (2002) 797.

[4] J. Rivas et al., Appl. Phys. Lett. 88 (2006) 242906.